VUSA003R350NA

Datasheet

General Description

$V_{(BR)DSS}$	$R_{DS(ON)\_max}$	I_D
30V	35mΩ@10V	4A
	55mΩ@4.5V	

Symbol

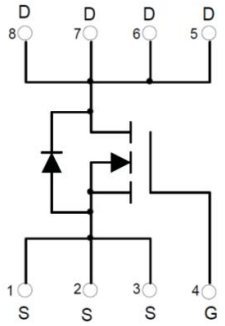
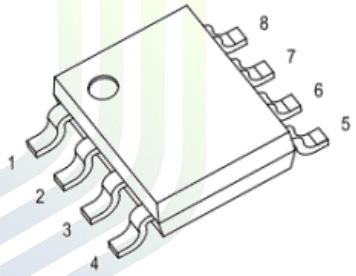


Figure 1 VUSA003R350NA

Features

- Trench Technology Power MOSFET
- Low Gate Charge
- Low $R_{DS(ON)}$

Package Type



SOP8

Figure 2 Package Type of VUSA003R350NA

Application

- Power Switch Application
- DC/DC Converters

Ordering Information

Product Name	Package
VUSA003R350NA	SOP8

Absolute Maximum Ratings (T_A= 25 ºC, unless otherwise specified)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current Note1	T_C= 25 ºC	I_D	4	A
Pulsed Drain Current Note2		I_{DM}	16	
Total Power Dissipation Note4	T_C= 25 ºC	P_D	1.4	W
Junction Temperature		T_J	150	ºC
Storage Temperature		T_{STG}	-55 to 150	ºC

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Ambient Note5	$R_{\theta JA}$		90		ºC/W

Electrical Characteristics (T_A= 25 ºC, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Statistic Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D= 250uA	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}= 30V, V_{GS}=0V			1	uA
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS}= 0V			±100	nA
Gate Threshold Voltage[Note3]	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1	1.7	2.5	V
Static Drain-Source On-Resistance[Note3]	$R_{DS(ON)}$	V_{GS}=10V, I_D= 4A		26	35	mΩ
		V_{GS}=4.5V, I_D= 3A		43	55	
Forward Transconductance[Note3]	g_{FS}	V_{DS}=5V, I_D= 3A	4			S
Dynamic Characteristics						
Input Capacitance	C_{ISS}	V_{DS}=20V		295		pF
Output Capacitance	C_{OSS}	V_{GS}=0V		42		pF
Reverse Transfer Capacitance	C_{RSS}	f=1MHz		34		pF
Total Gate Charge	Q_g	V_{DS}=15V		4		nC
Gate-Source Charge	Q_{gs}	V_{GS}=10V		1.3		
Gate-Drain Charge	Q_{gd}	I_D= 4A		1.6		
Gate Resistance	Rg	f = 1MHz, Open drain		1.5		Ω
Switching Parameters						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}= 15V		4.6		ns
Turn-on Rise Time	t_r	V_{GS}= 10V		2.7		
Turn-off Delay Time	$t_{d(off)}$	R_L=3Ω		15		
Turn-off Fall Time	t_f	R_G=2Ω		3.8		
Diode Characteristics						
Diode Forward Voltage [Note3]	V_{SD}	V_{GS}=0V, I_S= 4A			1.2	V

Notes :

1.The maximum current rating is limited by package.And device mounted on a large heatsink

2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.

3.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

4.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.And device mounted on a large heatsink

5.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

Typical Performance Characteristics

Figure 3: Transfer Characteristics

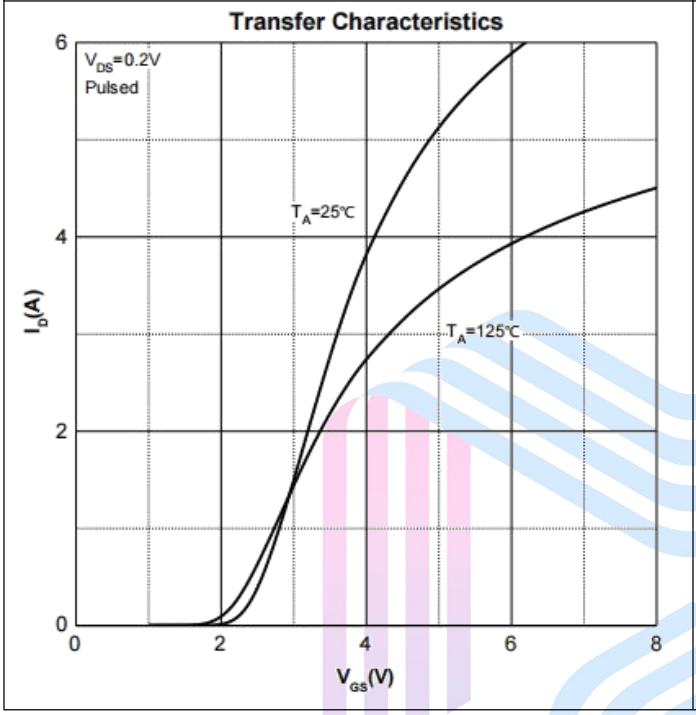


Figure 4: Output Characteristics

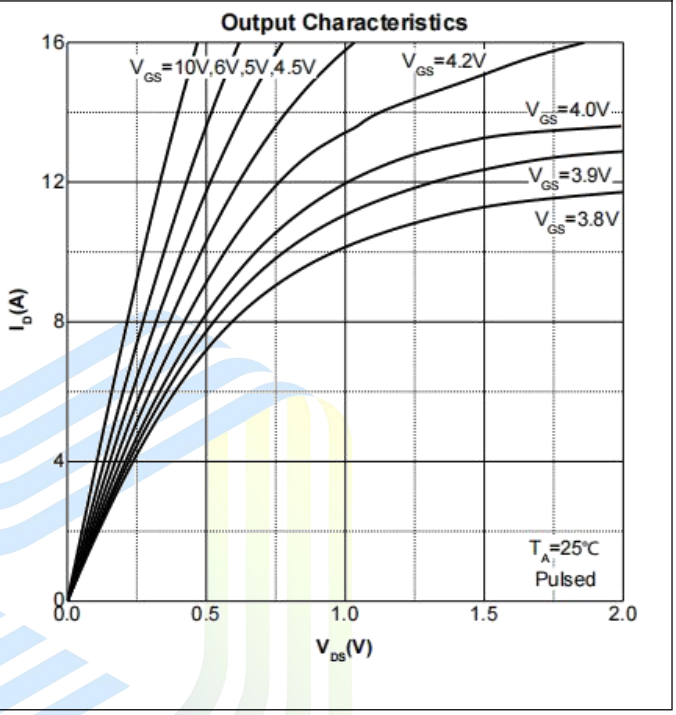


Figure 5: On-Resistance vs. Drain Current

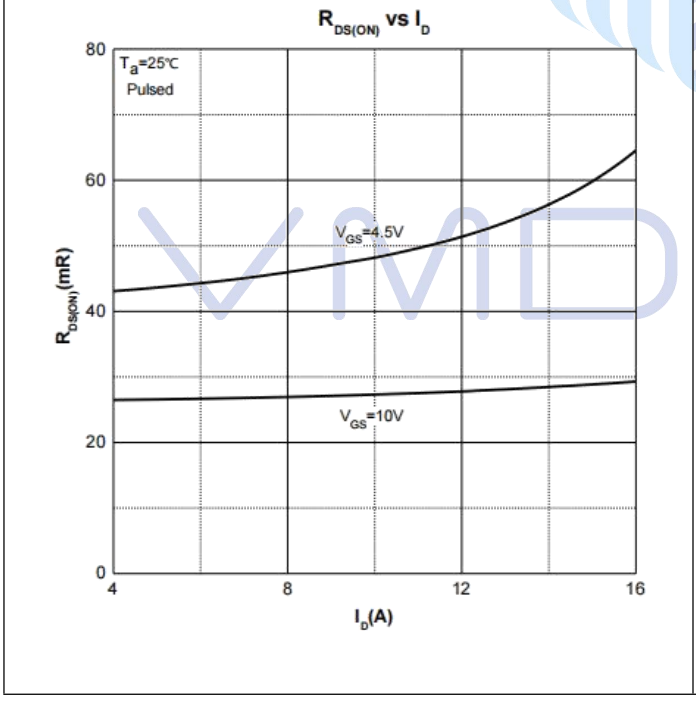


Figure 6: On-Resistance vs. Gate Voltage

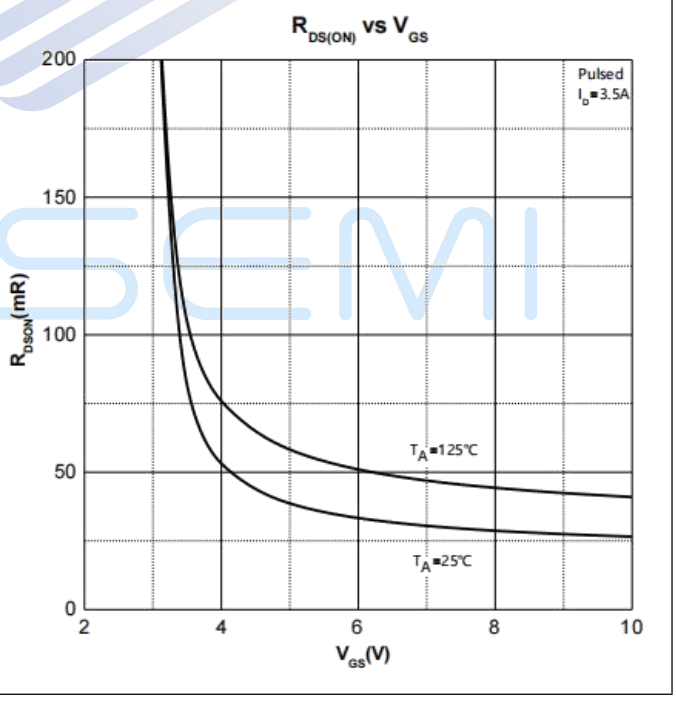


Figure 7: Body Diode Characteristics

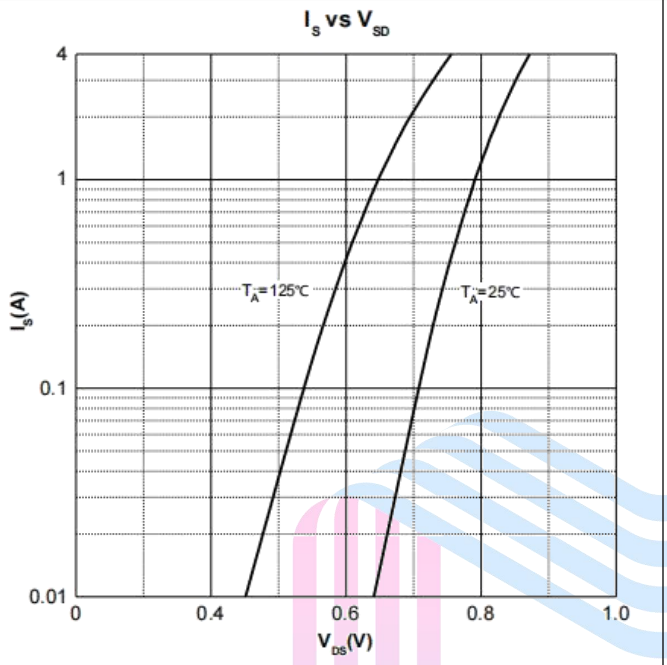
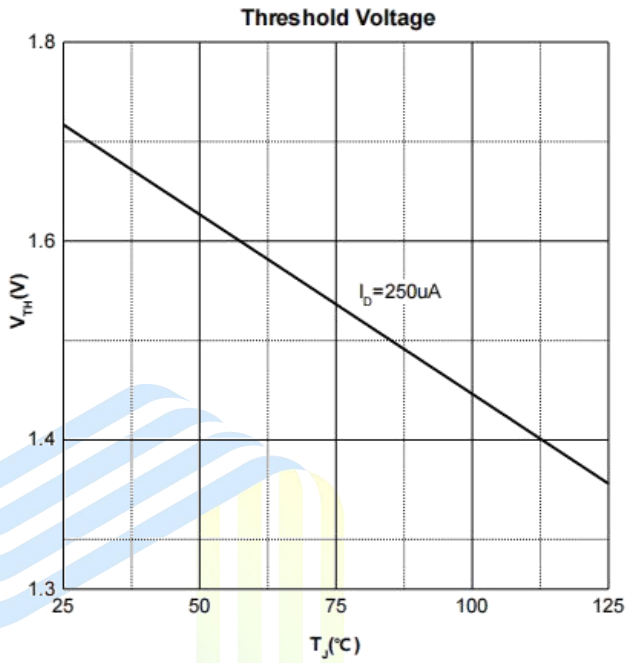
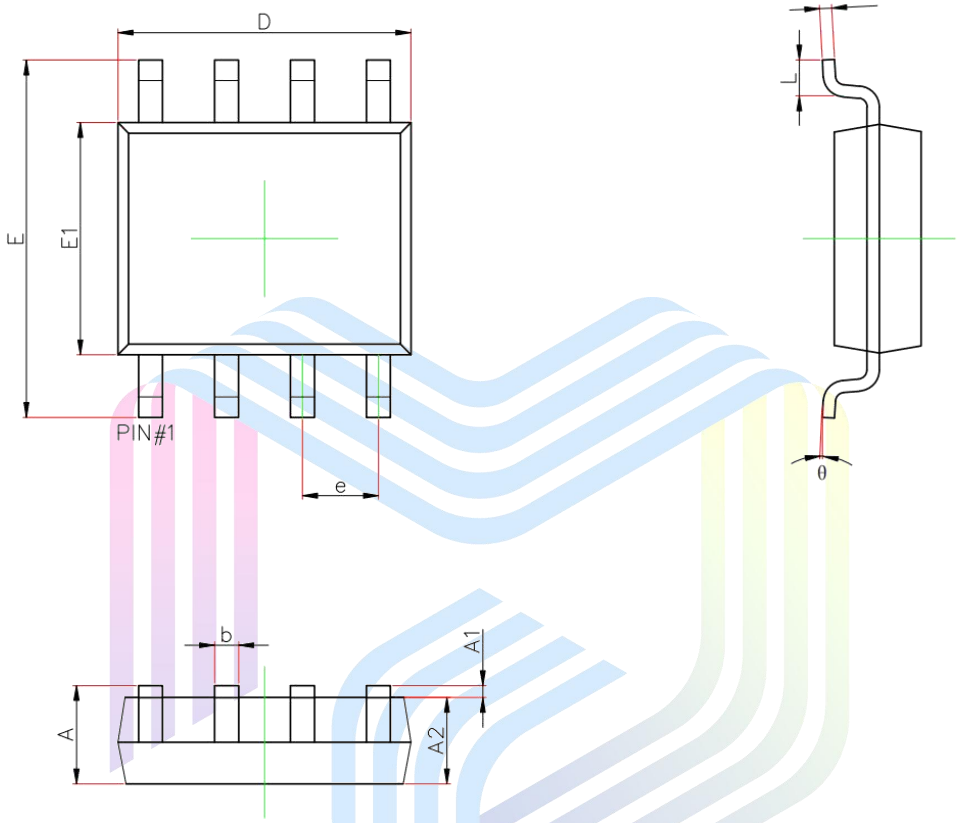


Figure 8: Threshold Voltage



Mechanical Dimensions:

SOP8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.156	0.250	0.006	0.010
D	4.700	5.100	0.185	0.201
e	1.270(BSC)		0.050(BSC)	
E	5.800	6.200	0.228	0.244
E1	3.700	4.100	0.146	0.161
L	0.400	1.270	0.016	0.05
θ	0°	8°	0°	8°

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